

**In the Claims:**

1-21 (canceled)

22 (currently amended) A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, comprising the steps ~~consisting essentially of~~:

forming a solution by combining HF with a concentration of about 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of from about 19% to about 30% in deionized water, ~~wherein~~ said forming a solution further consisting of ~~comprises using~~ a volume ratio of from about 1 to 3 parts HF, from about 1 to 2 parts H<sub>2</sub>O<sub>2</sub> and from about 10 to about 30 parts deionized water ~~greater than 1:1:20 of HF:H<sub>2</sub>O<sub>2</sub>:deionized water~~; and

applying said solution to said semiconductor body with said solution being at at least about room temperature.

23 (canceled)

24 (currently amended) A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, comprising the steps of ~~consisting essentially of~~:

forming a solution by combining HF with a concentration of about 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of about ~~29%~~ 30% in deionized water, ~~wherein~~ said forming a solution further consisting of ~~comprises using~~ a volume ratio of about 2 parts HF, about 1 part H<sub>2</sub>O<sub>2</sub> and about 21 parts ~~2:1:21 of HF:H<sub>2</sub>O<sub>2</sub>:deionized water~~; and

applying said solution to said semiconductor body with said solution being at about room temperature.

25 (previously presented) The method of claim 22 wherein said method further comprises applying said solution in the presence of photoresist.

26. (currently amended) A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, comprising the steps of ~~consisting essentially of~~:

forming a solution by combining HF with a concentration of about 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of about 29%-30% in deionized water wherein said forming a solution further consists of ~~comprises~~ using a volume ratio greater than about 1 part HF, about 1 part H<sub>2</sub>O<sub>2</sub> and about 20 parts ~~1:1:20 of HF:H<sub>2</sub>O<sub>2</sub>:deionized water~~; and

applying said solution to said semiconductor body with said solution being at a temperature of 40°C to 50°C.

27 (canceled)

28. (currently amended) A method for etching one or more of the following: TaN, TiN, Cu, FSG, TEOS, and SiN from a semiconductor body in semiconductor device processing, comprising the steps ~~consisting essentially of~~:

forming a solution by combining HF with a concentration of about 49% with H<sub>2</sub>O<sub>2</sub> with a concentration of about 29%-30% in deionized water wherein said forming a solution further consists of ~~comprises~~ using a volume ratio of about 2 part HF, about 1 part H<sub>2</sub>O<sub>2</sub> and about 21 parts ~~2:1:21 of HF:H<sub>2</sub>O<sub>2</sub>:deionized water~~; and

applying said solution to said semiconductor body with said solution being at a temperature of from about 40°C to about 50°C.

29. (previously presented) The method of claim 26 wherein said method further comprises applying said solution in the presence of photoresist.

30. (previously presented) The method of claim 28 wherein said method further comprises applying said solution in the presence of photoresist.

31. (previously presented) The method of claim 24 wherein said method further comprises applying said solution in the presence of photoresist.